

MiniSKiiP<sup>®</sup> 1

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter

SKiiP 11NAB065V1

### Features

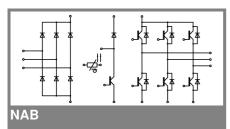
- Ultrafast NPT IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

## **Typical Applications\***

- Inverter up to 3,5 kVA
- Typical motor power 1,5 kW

### Remarks

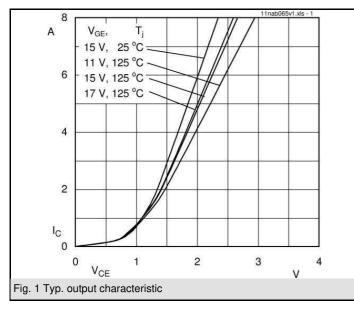
• V<sub>CEsat</sub> , V<sub>F</sub> = chip level value

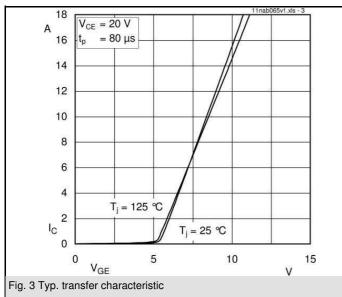


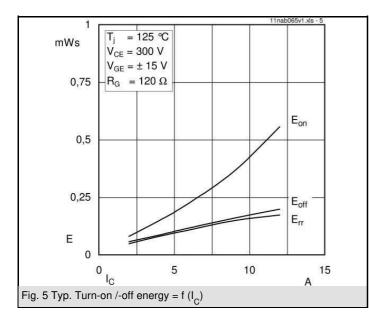
Absolute	Maximum Ratings	$T_s = 25 \text{ °C}$ , unless otherwise specified						
Symbol	Conditions	Values	Units					
IGBT - Inverter, Chopper								
V <sub>CES</sub>		600	V					
I <sub>C</sub>	T <sub>s</sub> = 25 (70) °C	12 (10)	Α					
I <sub>CRM</sub>		12	А					
V <sub>GES</sub>		± 20	V					
Т <sub>ј</sub>		- 40 + 150	°C					
Diode - Inverter, Chopper								
I <sub>F</sub>	T <sub>s</sub> = 25 (70) °C	12 (12)	А					
I <sub>FRM</sub>		12	А					
Т <sub>ј</sub>		- 40 + 150	°C					
Diode - Rectifier								
V <sub>RRM</sub>		800	V					
I <sub>F</sub>	T <sub>s</sub> = 70 °C	35	А					
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms, sin 180 °, T <sub>j</sub> = 25 °C	220	Α					
i²t	t <sub>p</sub> = 10 ms, sin 180 °, T <sub>j</sub> = 25 °C	240	A²s					
Т <sub>ј</sub>		- 40 + 150	°C					
Module	•		•					
I <sub>tRMS</sub>	per power terminal (20 A / spring)	20	А					
T <sub>stg</sub>		- 40 + 125	°C					
V <sub>isol</sub>	AC, 1 min.	2500	V					

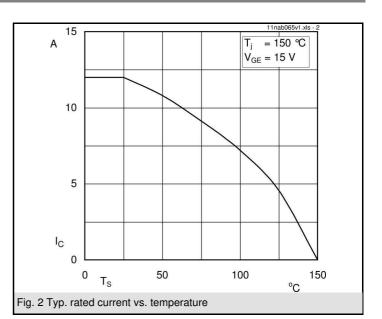
Characteristics T <sub>s</sub> = 25 °C, unless otherwise specir									
Symbol	Conditions	min.	typ.	max.	Units				
IGBT - Inverter, Chopper									
V <sub>CEsat</sub>	I <sub>Cnom</sub> = 6 A, T <sub>j</sub> = 25 (125) °C		2 (2,2)	2,5 (2,7)	V				
V <sub>GE(th)</sub>	$V_{GE} = V_{CE}, I_{C} = 0.5 \text{ mA}$	3	4	5	V				
V <sub>CE(TO)</sub>	$T_j = 25 (125) °C$		1,2 (1,1)	,	V				
r <sub>T</sub>	$T_{j} = 25 (125) °C$		133 (183)	200 (250)	mΩ				
C <sub>ies</sub>	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,32		nF				
C <sub>oes</sub>	$V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz$		0,08		nF				
C <sub>res</sub>	$V_{CE} = 25 \text{ V}, \text{ V}_{GE} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		0,03		nF				
R <sub>th(j-s)</sub>	per IGBT		1,9		K/W				
t <sub>d(on)</sub>	under following conditions		25		ns				
t <sub>r</sub>	$V_{CC} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}$		30		ns				
t <sub>d(off)</sub>	$I_{Cnom} = 6 \text{ A}, T_j = 125^{\circ}\text{C}$		195		ns				
t <sub>r</sub>	$R_{Gon} = R_{Goff} = 120 \Omega$		20 0,22		ns				
E <sub>on</sub>	inductive load		0,22		mJ				
E <sub>off</sub>			0,12		mJ				
	verter, Chopper								
$V_F = V_{EC}$	I <sub>Fnom</sub> = 6 A, T <sub>j</sub> = 25 (125) °C		1,3 (1,2)	1,5 (1,4)	V				
V <sub>(TO)</sub>	T <sub>j</sub> = 25 (125) °C		1 (0,9)	1,1 (1)	V				
r <sub>T</sub>	T <sub>j</sub> = 25 (125) °C		45 (50)	60 (70)	mΩ				
R <sub>th(j-s)</sub>	per diode		2,5		K/W				
I <sub>RRM</sub>	under following conditions		8,3		Α				
Q <sub>rr</sub>	I <sub>Fnom</sub> = 6 A, V <sub>R</sub> = 300 V		0,6		μC				
Err	V <sub>GE</sub> = 0 V, T <sub>j</sub> = 125 °C		0,11		mJ				
	di <sub>F</sub> /dt = 430 A/µs								
Diode - R	ectifier	•							
V <sub>F</sub>	I <sub>Enom</sub> = 15 A, T <sub>i</sub> = 25 °C		1,1		V				
V <sub>(TO)</sub>	T <sub>i</sub> = 150 °C		0,8						
r <sub>T</sub>	T <sub>j</sub> = 150 °C		20						
R <sub>th(j-s)</sub>	per diode		1,5		K/W				
	ure Sensor				•				
R <sub>ts</sub>	3 %, T <sub>r</sub> = 25 (100) °C		1000(1670)		Ω				
Mechanical Data									
w			35		g				
M <sub>s</sub>	Mounting torque	2		2,5	Nm				

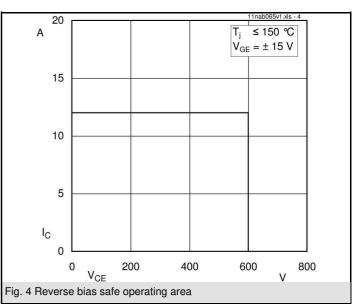
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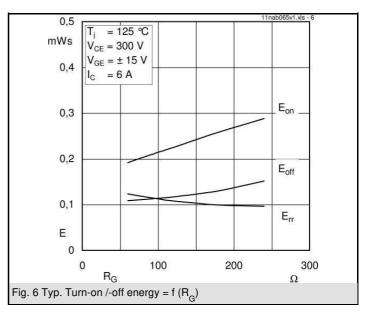


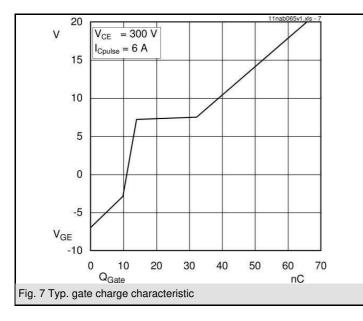


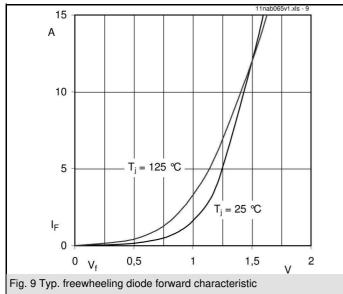


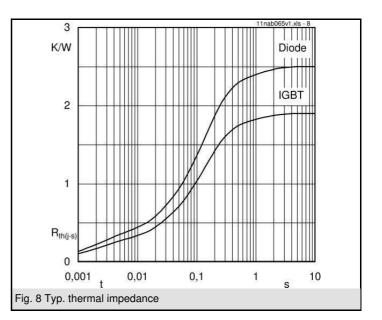


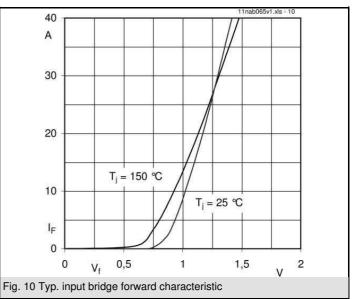


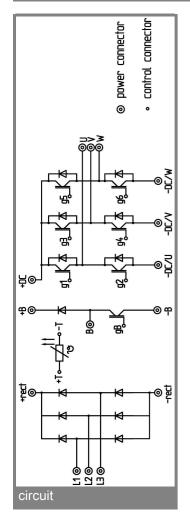


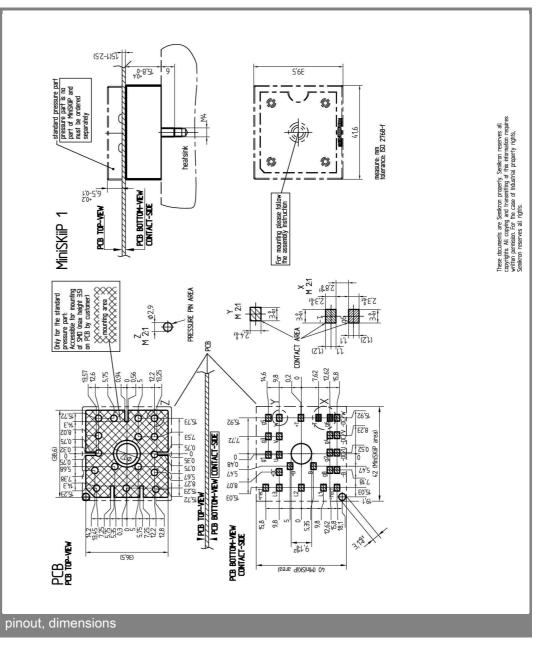












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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